

United States Patent and Trademark Office

UNITED STATES DEPARTMENT OF COMMERCE United States Patent and Trademark Office Address: COMMISSIONER FOR PATENTS P.O. Box 1450 Alexandria, Virginia 22313-1450 www.uspto.gov

APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/707,119	11/21/2003	Lawrence A. Clevenger	FIS920030219US1	1118	
32074	7590 06/22/2005		EXAMINER		
INTERNAT	TIONAL BUSINESS MA	DANG, PHUC T			
DEPT. 18G			<u> </u>		
BLDG. 300-482			ART UNIT	PAPER NUMBER	
2070 ROUTE 52			2818		
HOPEWELL	JUNCTION, NY 12533				

DATE MAILED: 06/22/2005

Please find below and/or attached an Office communication concerning this application or proceeding.

Office Action Summary		Application No. 10/707,119		Applicant(s)					
				CLEVENGER ET AL.		(cm)			
		Examiner		Art Unit					
		PHUC T. DAN		2818		·			
Period fo	The MAILING DATE of this communication app or Reply	ears on the co	ver sheet with the co	errespondence ac	idress				
THE - Exte after - If the - If NC - Failu Any	ORTENED STATUTORY PERIOD FOR REPLY MAILING DATE OF THIS COMMUNICATION. nsions of time may be available under the provisions of 37 CFR 1.13 SIX (6) MONTHS from the mailing date of this communication. e period for reply specified above is less than thirty (30) days, a reply period for reply is specified above, the maximum statutory period were to reply within the set or extended period for reply will, by statute reply received by the Office later than three months after the mailing ed patent term adjustment. See 37 CFR 1.704(b).	36(a). In no event, h y within the statutory will apply and will exp , cause the application	nowever, may a reply be time minimum of thirty (30) days pire SIX (6) MONTHS from the on to become ABANDONED	ely filed will be considered time ne mailing date of this o (35 U.S.C. § 133).	•	1.			
Status		•							
1)⊠	Responsive to communication(s) filed on election filed on April 11, 2005.								
2a) <u></u> □	2a) ☐ This action is FINAL. 2b) ☑ This action is non-final.								
3) Since this application is in condition for allowance except for formal matters, prosecution as to the merits is									
closed in accordance with the practice under Ex parte Quayle, 1935 C.D. 11, 453 O.G. 213.									
Disposit	ion of Claims								
4) 🖂	Claim(s) 1-22 is/are pending in the application.	•							
	4a) Of the above claim(s) <u>12-22</u> is/are withdrawn from consideration.								
5)	5) ☐ Claim(s) is/are allowed. 6) ☑ Claim(s) <u>1,3,5 and 9</u> is/are rejected.								
•	7)⊠ Claim(s) <u>2,4,6-8,10 and 11</u> is/are objected to.								
8)	Claim(s) are subject to restriction and/o	r election requ	iirement.						
Applicat	ion Papers	•							
9) 🗌	The specification is objected to by the Examine	er.							
10)⊠ The drawing(s) filed on <u>21 November 2003</u> is/are: a)⊠ accepted or b)□ objected to by the Examiner.									
	Applicant may not request that any objection to the								
	Replacement drawing sheet(s) including the correct					1).			
11)[_]	The oath or declaration is objected to by the Ex	xaminer. Note	the attached Office	Action or form P	TO-152.				
Priority	under 35 U.S.C. § 119								
12)	Acknowledgment is made of a claim for foreign	priority under	35 U.S.C. § 119(a)-	-(d) or (f).					
a) All b) Some * c) None of:									
1. Certified copies of the priority documents have been received.									
	2. Certified copies of the priority document								
	3. Copies of the certified copies of the prio			d in this National	l Stage				
* 1	application from the International Bureau See the attached detailed Office action for a list	•		d					
~ `	See the attached detailed Office action for a list	or the certified	a cobies not received	u.					
A 44 - *									
Attachmer	ce of References Cited (PTO-892)	4)	☐ Interview Summary	(PTQ-413)					
2) Notice	ce of Draftsperson's Patent Drawing Review (PTO-948)	-	Paper No(s)/Mail Da	te	O 450\				
• —	rmation Disclosure Statement(s) (PTO-1449 or PTO/SB/08) er No(s)/Mail Date <u>112103</u> .	5) 6)	☐ Notice of Informal Pa	atent Application (PT	U-13 <i>2)</i>				
•									

Application/Control Number: 10/707,119 Page 2

Art Unit: 2818

DETAILED ACTION

Restriction/election

1. Applicant's election without traverse of Group I (claims 1-11) filed on April 11, 2005, drawn to a method of forming a layer of interconnect in an integrated circuit and withdrawn Group II (claims 12-22).

Applicants have the right to file a divisional application covering the subject matter of the non-elected claims.

Information Disclosure Statement

2. The office acknowledges receipt of the following items from the applicant: Information Disclosure Statement (IDS) filed on November 21, 2003.

Specification

3. The specification has been checked to the extent necessary to determine the presence of all possible minor errors. However, the applicant's cooperation is requested in correcting any errors of which applicant may become aware in the specification.

Claim Objections

4. Claim 1 is objected to because of the following reason:

In claim 1, insert "(ILD)" after – a first layer of interlayer dielectric --.

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

5. Claims 1 is rejected under 35 U.S.C. 103(a) as being unpatentable over Nakagawa et al., hereinafter "Nakagawa" (U.S. Patent No. 6,562,710 B2 in view of Kimock et al., hereinafter "Kimock" (U.S. Patent No. 5,135,808).

Regarding claim 1, Nakagawa discloses a method for fabricating a semiconductor device comprising the steps of:

depositing a first layer of interlayer dielectric (ILD) (111, Fig. 2C) on a lower layer of the integrated circuit above a set of lower alignment marks (109a, Fig. 2C);

depositing a first hardmask layer (112, Fig. 2C) on the first layer of ILD (11, Fig. 2C); forming an upper set of alignment marks (114a, Fig. 3C);

patterning the ILD (111, Fig. 3A) through the hardmask layer (112, Fig. 3A) to form a set of apertures (111a, Fig. 3A) in the ILD (111, Fig. 3A); and

forming a conductive interconnect (11e, Fig. 3B) in the set of apertures (111a, Fig. 3B).

Nakagawa discloses all the features of the claimed invention as discussed above, but does not disclose the first hardmask comprises of TaN on the first layer of ILD and the first layer being substantially transparent in a relevant wavelength range.

Art Unit: 2818

Kimock, however, discloses the first hardmask comprises of TaN on the first layer of ILD and the first layer being substantially transparent in a relevant wavelength range [col. 11, line 64-col. 12, line 11].

It would have been obvious to one having ordinary skilled in the art at the time the invention was made to modify the above discussed teaching of Nakagawa as taught by Kimock for a purpose of improving a process of fabricating a semiconductor device.

6. Claims 3, 5 and 9 are rejected under 35 U.S.C. 103(a) as being unpatentable over Nakagawa and Kimock in view of Kasahara (U.S. Patent No. 6,358,766 B1).

Regarding claims 3, 5 and 9, Nakagawa discloses all the features of the claimed invention as discussed above, but does not disclose the hardmask layer has a thickness ranging from 5 nm to 100 nm and the hardmask is deposited by chemical vapor deposition by reacting a precursor containing Ta in an ambient containing N₂ and substantially transparent in the relevant wavelength range.

Kasahara, however, discloses the hardmask layer has a thickness ranging from 5 nm to 100 nm and the hardmask is deposited by chemical vapor deposition by reacting a precursor containing Ta in an ambient containing N₂ and substantially transparent in the relevant wavelength range [col. 12, lines 61-63 and col. 19, line 19-col. 20, line 11].

It would have been obvious to one having ordinary skilled in the art at the time the invention was made to modify the above discussed teaching of Nakagawa as taught by Kasahara for a purpose of improving a process of fabricating a semiconductor device.

Allowable Subject Matter

7. The following is a statement of reason for the indication of allowable subject matter:

Claims 2, 4, 6-8 and 10-11 are objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claim.

None of the prior art made of record does not disclose the hardmask layer is deposited by sputter deposition of Ta in an ambient containing N2 and a carrier gas such that (N2 flow)/(N2 + carrier flow) > 0.5 as cited in claim 2 and the hardmask layer has a resistivity greater than about 400 Ohms-cm as cited in claim 4 and the hardmask layer has a composition of less than 50% Ta as cited in claim 11.

Claims 4, 6, 8 and 10 are depend on claim 2, then, they also would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claim.

Conclusion

- Applicants are advised to cancel the non-elected claims of Group II (claims 11-22) in 7. response upon to the next Office action if the application is considered to be allowed.
- The prior art made of record and not relied upon is considered pertinent to applicant's 8. disclosure. Sugiyama'614 and Komuro'328 are cited interest.
- Any inquiry concerning this communication or earlier communications from the examiner should be directed to Phuc T. Dang whose telephone number is (571) 272-1776. The examiner can normally be reached on 8:00 am-5:00 pm.

Application/Control Number: 10/707,119

Page 6

Art Unit: 2818

- 10. If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, David C. Nelms can be reached on (571) 272-1787. The fax phone numbers for the organization where this application or proceeding is assigned are 703-872-9306 for regular communications and After Final communications.
- 11. Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is 703-308-0956.

Langshow

PD

Phuc T. Dang

Primary Examiner

Art Unit 2818